Silicon PNP Power Transistors 2SA1726

DESCRIPTION

·With TO-220C package

·Complement to type 2SC4512

APPLICATIONS

·Audio and General Purpose

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

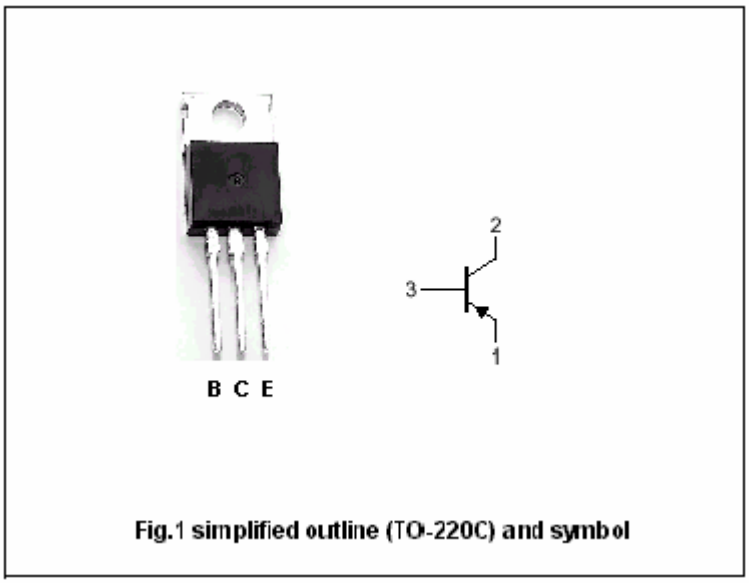


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-6	A
I_B	Base current		-3	A
P_C	Collector dissipation	T_C=25□	50	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-25mA; R_{BE}=∞	-80			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=-2A; I_B=-0.2A			-0.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-80V ;I_E=0			-10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-10	μA
h_{FE}	DC current gain	I_C=-2A ; V_{CE}=-4V	50		180	
C_{OB}	Collertor output capacitance	f=1MHz; V_{CB}=-10V		150		pF
f_T	Transition frequency	I_E=0.5A ; V_{CE}=-12V		20		MHz
Switching times						
t_{on}	Turn-on time	V_{CC}=-30V; I_C=-3A I_{B1}=-I_{B2}=-0.3A R_L=10Ω		0.18		μs
t_{stg}	Storage time			1.10		μs
t_f	Fall time			0.21		μs

◆ h_{FE} Classifications

O	P	Y
50-100	70-140	90-180

PACKAGE OUTLINE

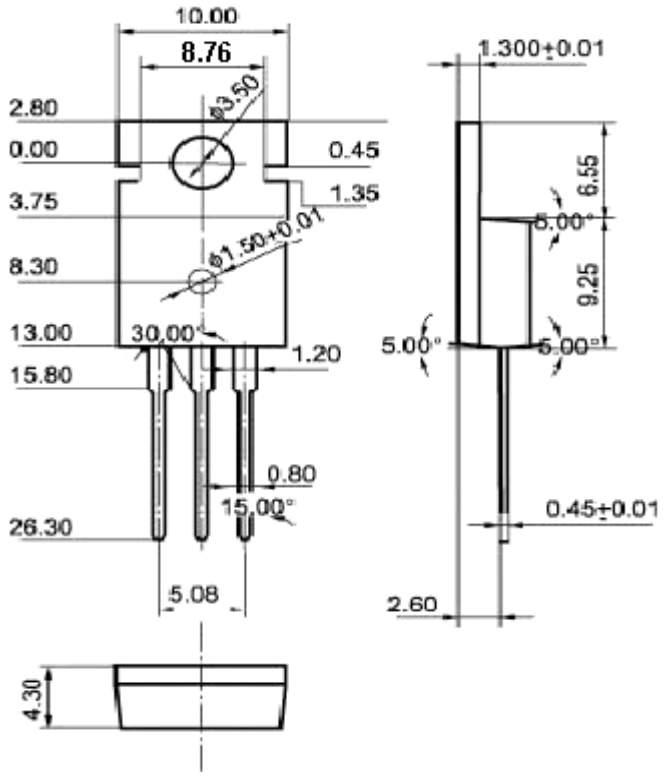


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)

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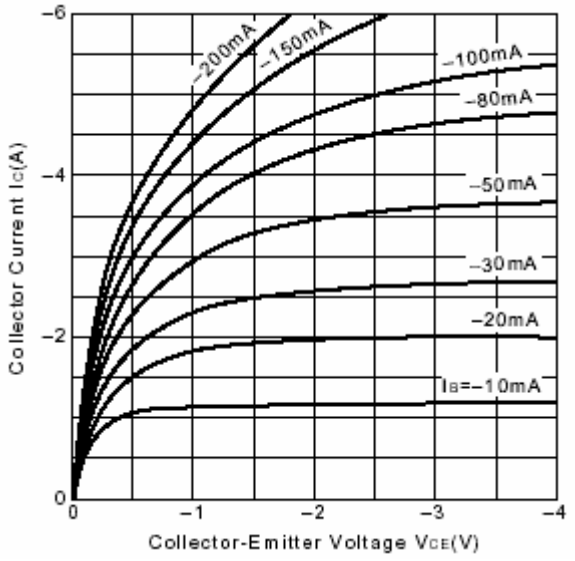


Fig.3 Static Characteristic

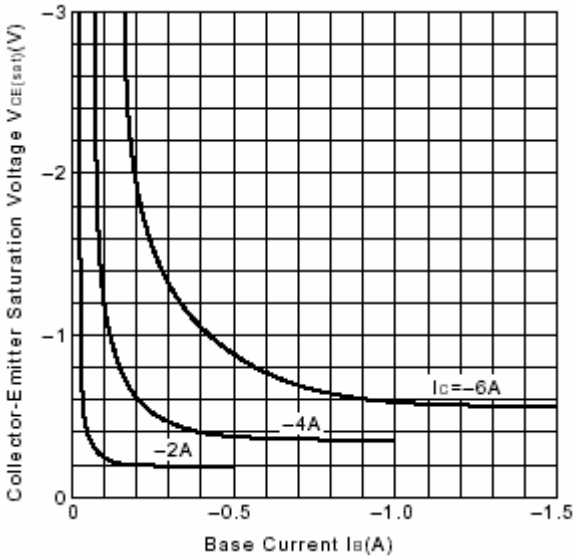


Fig.4 $V_{CE}(sat)-I_B$ Characteristics

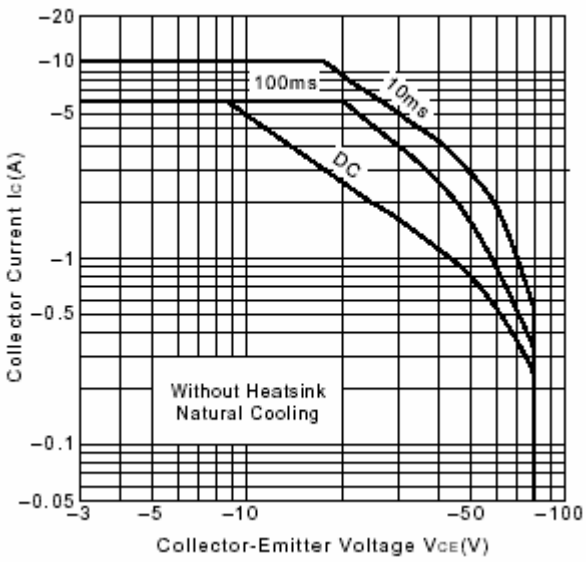


Fig.5 Safe Operating Area

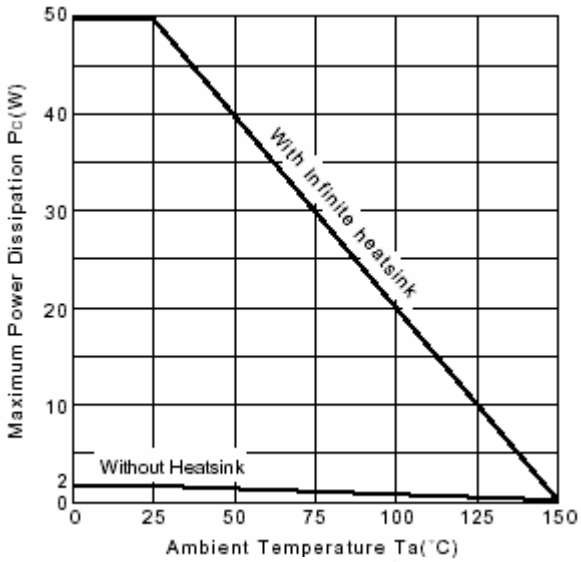


Fig.6 Pc-Ta Derating

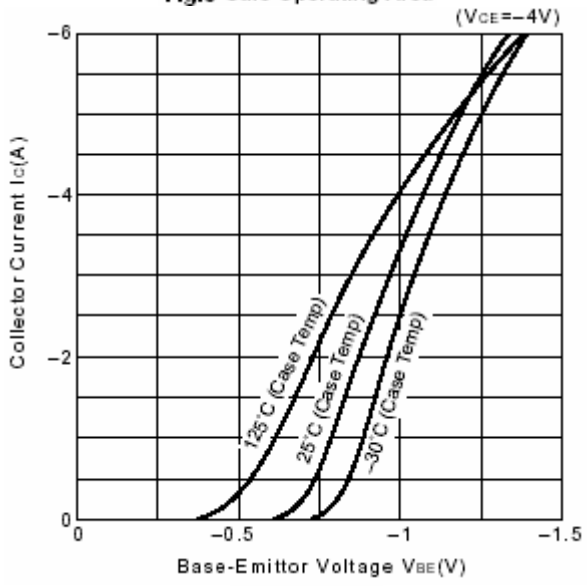


Fig.7 I_C-V_{BE}

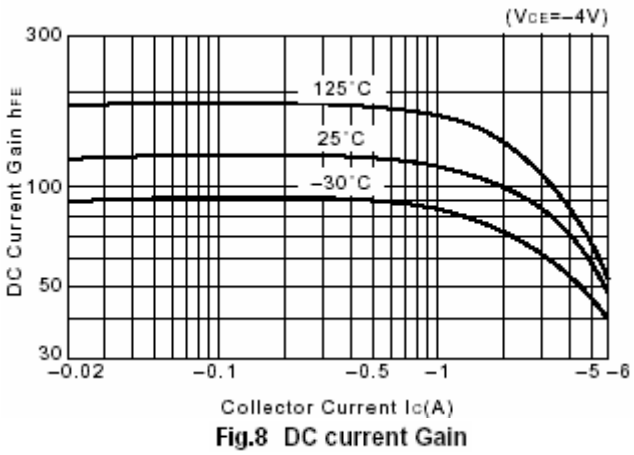


Fig.8 DC current Gain